

/ Descriptions

TO-263 N

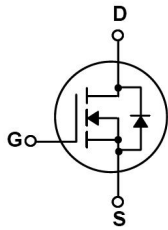
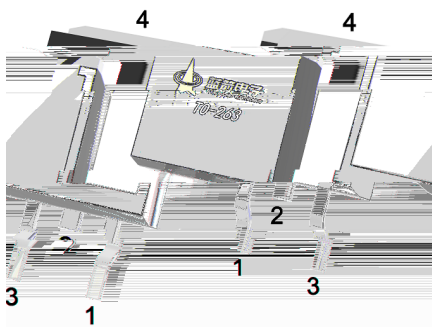
N-CHANNEL MOSFET in a TO-263 Plastic Package.

/ Features $V_{DS}=60V$ $I_D=225A$ $R_{DS(on)}@10V \leq 2.2m\Omega$ (Type. 1.9m Ω) $R_{DS(on)}@4.5V \leq 3.5m\Omega$ (Type. 2.5m Ω)

HF Product.

/ Applications

These devices are well suited for high efficient switched mode power supplies Active power factor correction, electronic lamp ballast based on half bridge topology.

/ Equivalent Circuit**/ Pinning**

PIN1 G PIN 2 4 D PIN 3 S

/ Marking

See Marking Instructions.

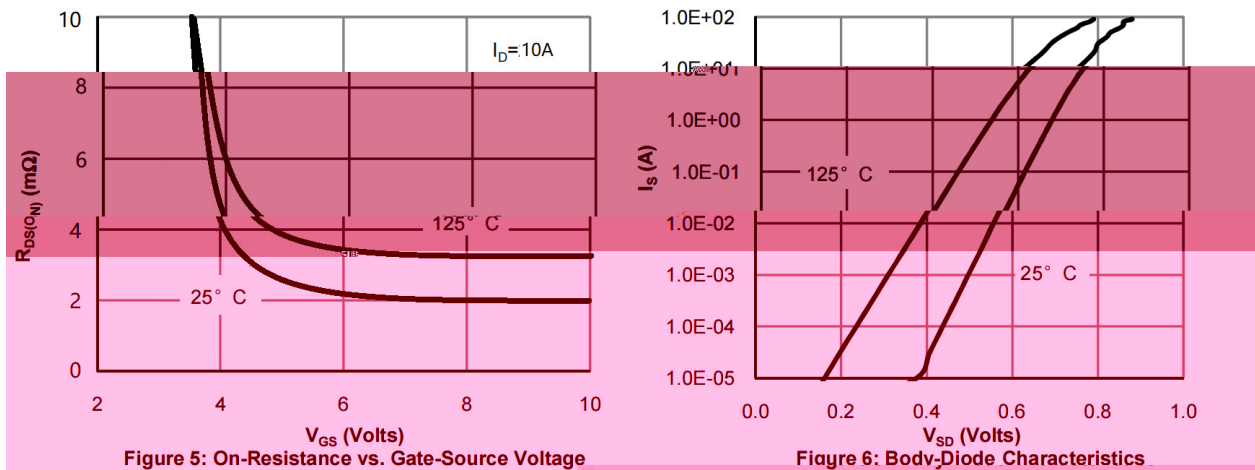
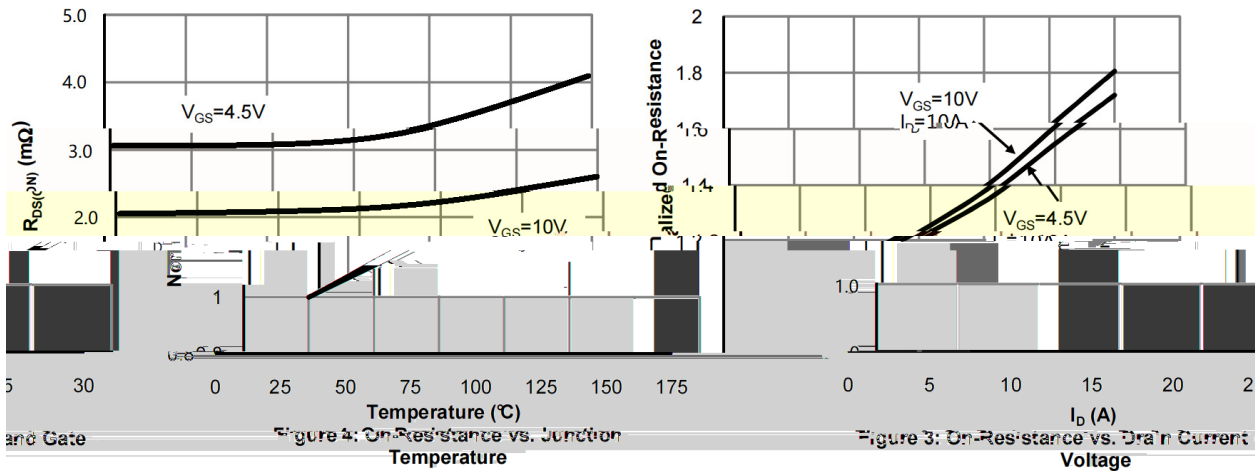
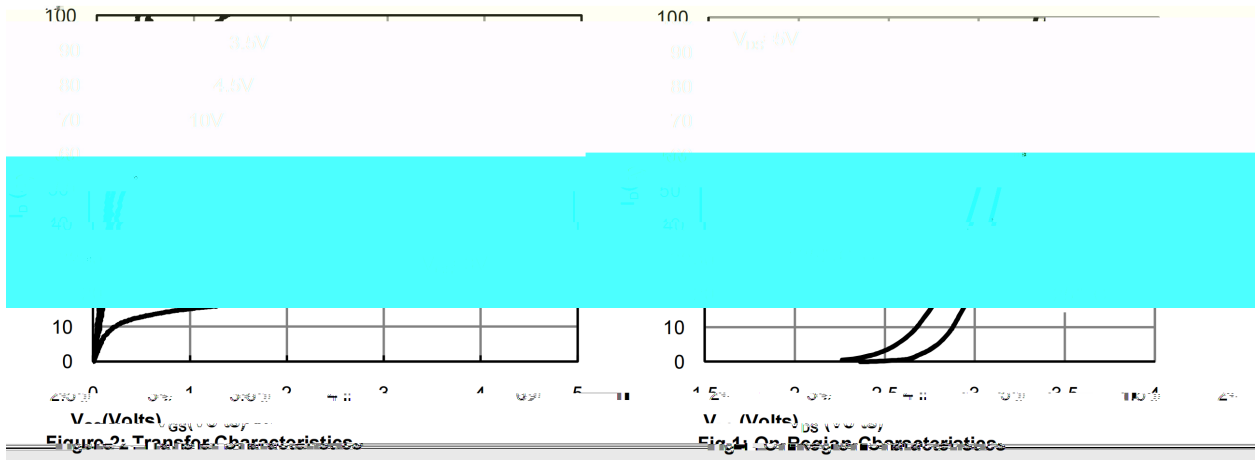
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	60	V
Drain Current		$I_D(T_C=25^\circ\text{C})$	225	A
Pulsed Drain Current		I_{DM}	646	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy $L=0.5\text{mH}$		E_{AS}	380	mJ
Avalanche Current		I_{AS}	30.8	A
Total Power Dissipation		$P_D(T_C=25^\circ\text{C})$	125	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	Steady-State	$R_{\theta JA}$	50	/W
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.63	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	60	65		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=10A$		1.9	2.2	m Ω
		$V_{GS}=4.5V$ $I_D=10A$		2.5	3.5	
Forward On Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_g(10V)$	$V_{GS}=10V$ $V_{DS}=30V$ $I_D=20A$		60		nC
Total Gate Charge	$Q_g(4.5V)$			23		
Gate Source Charge	Q_{gs}			16		
Gate Drain Charge	Q_{gd}			3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_L=1\Omega$ $R_{GEN}=3\Omega$		13		ns
Turn-On Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			47		
Turn-Off Fall Time	t_f			6.5		

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve

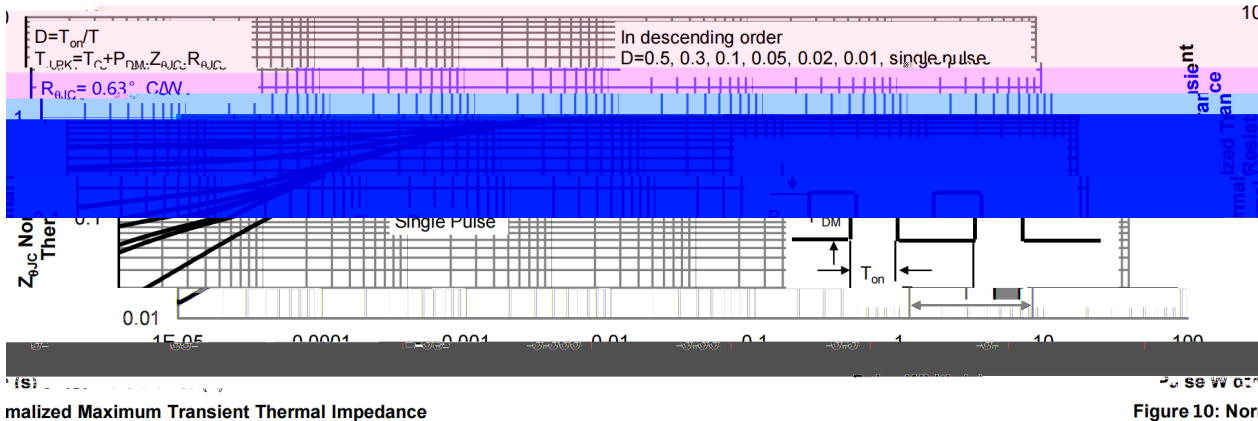
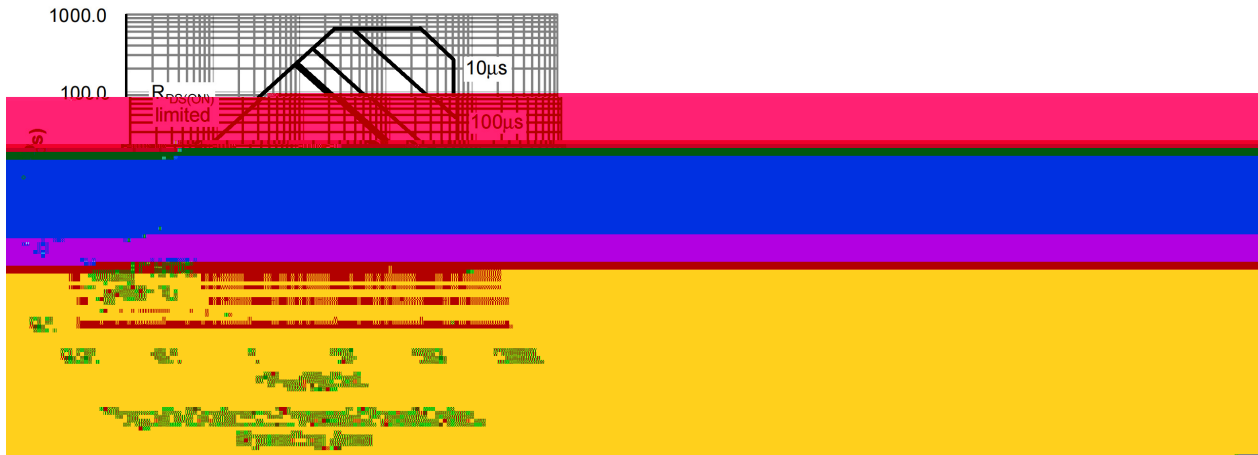
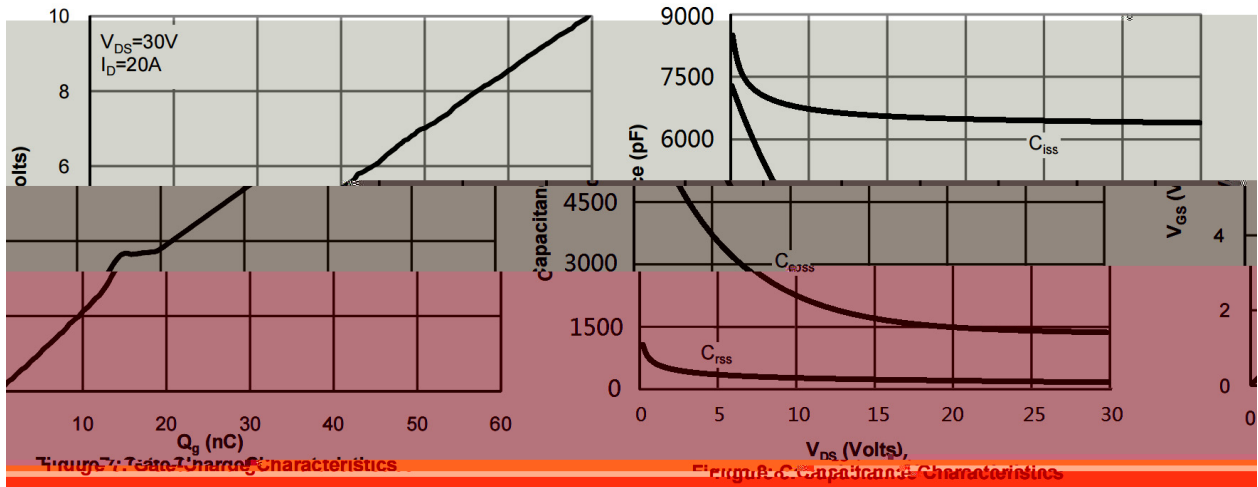
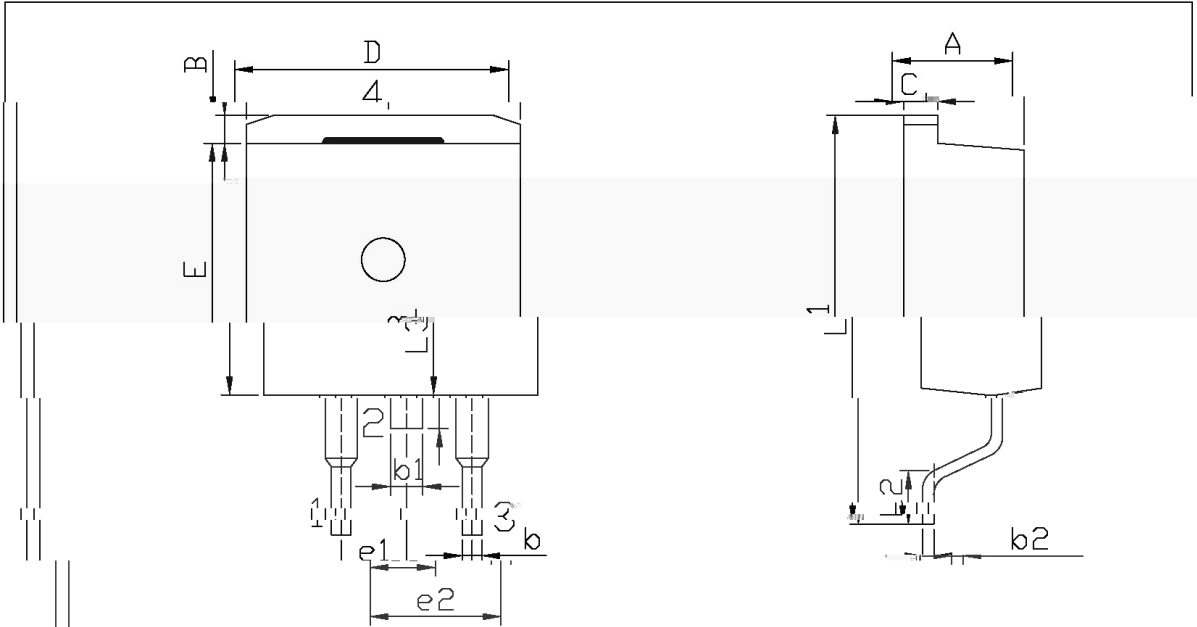


Figure 10: Normalized Maximum Transient Thermal Impedance

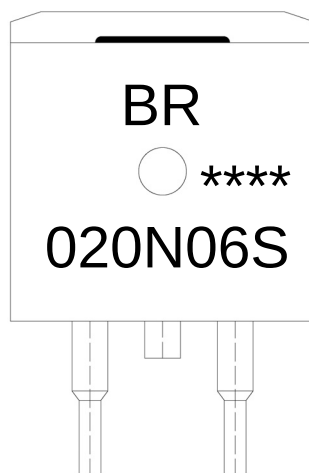
Figure 10: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions



单位: mm								
mmeters			Dimensions In Millimeters			Dimensions In Millimeters		
			Symbol	Min	Max	Symbol	Min	Max
ax			A	4.30	4.70	E _L	0.00	0.00
40			B	1.00	1.40	e1	2.34	2.34
74			b	0.70	0.90	e2	4.88	5.08
28								

/ Marking Instructions



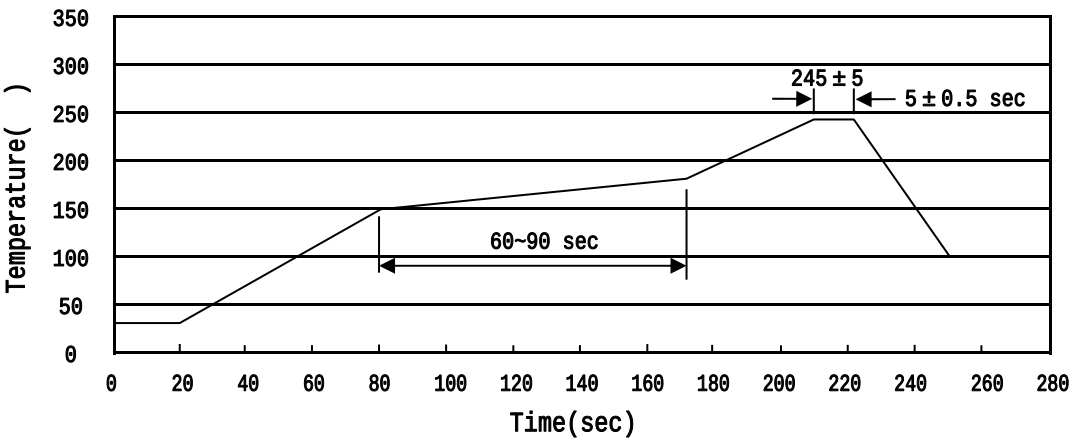
Note:

BR: Company Code

020N06S: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-263	800	1	800	6	4,800	13 ×24	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

/ Notices